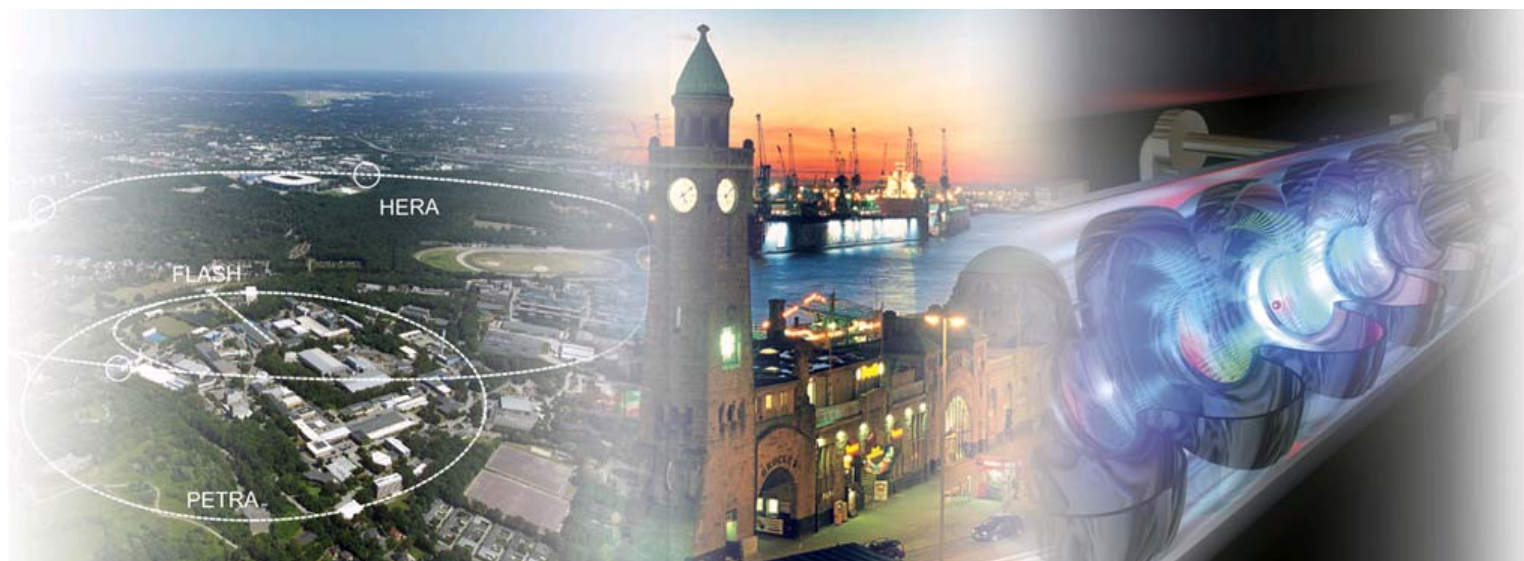


A 10-bits pipeline ADC dedicated to the VFE Electronics of Si-W Ecal

Laurent Royer, G. Bohner, R. Cornat, P. Gay, J. Lecoq, S. Manen
IN2P3/LPC Clermont-Ferrand
in Collaboration with LAL (Orsay)

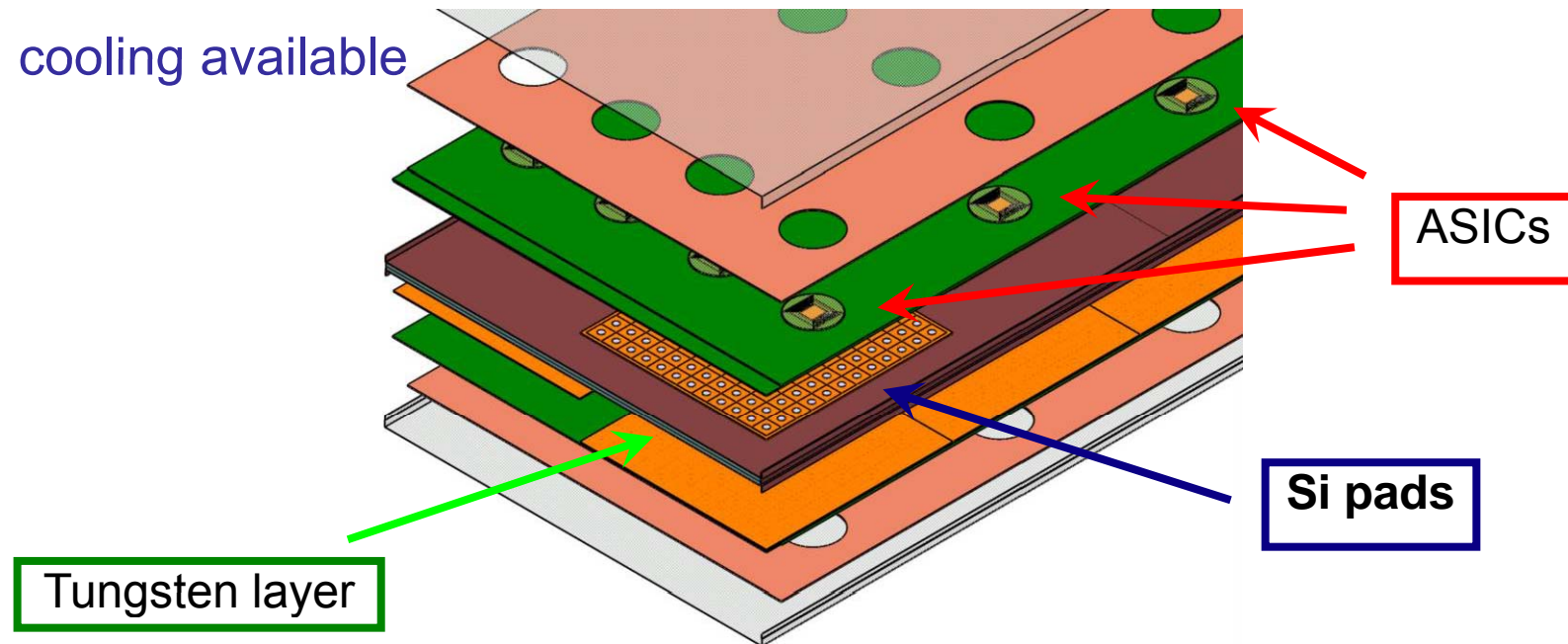


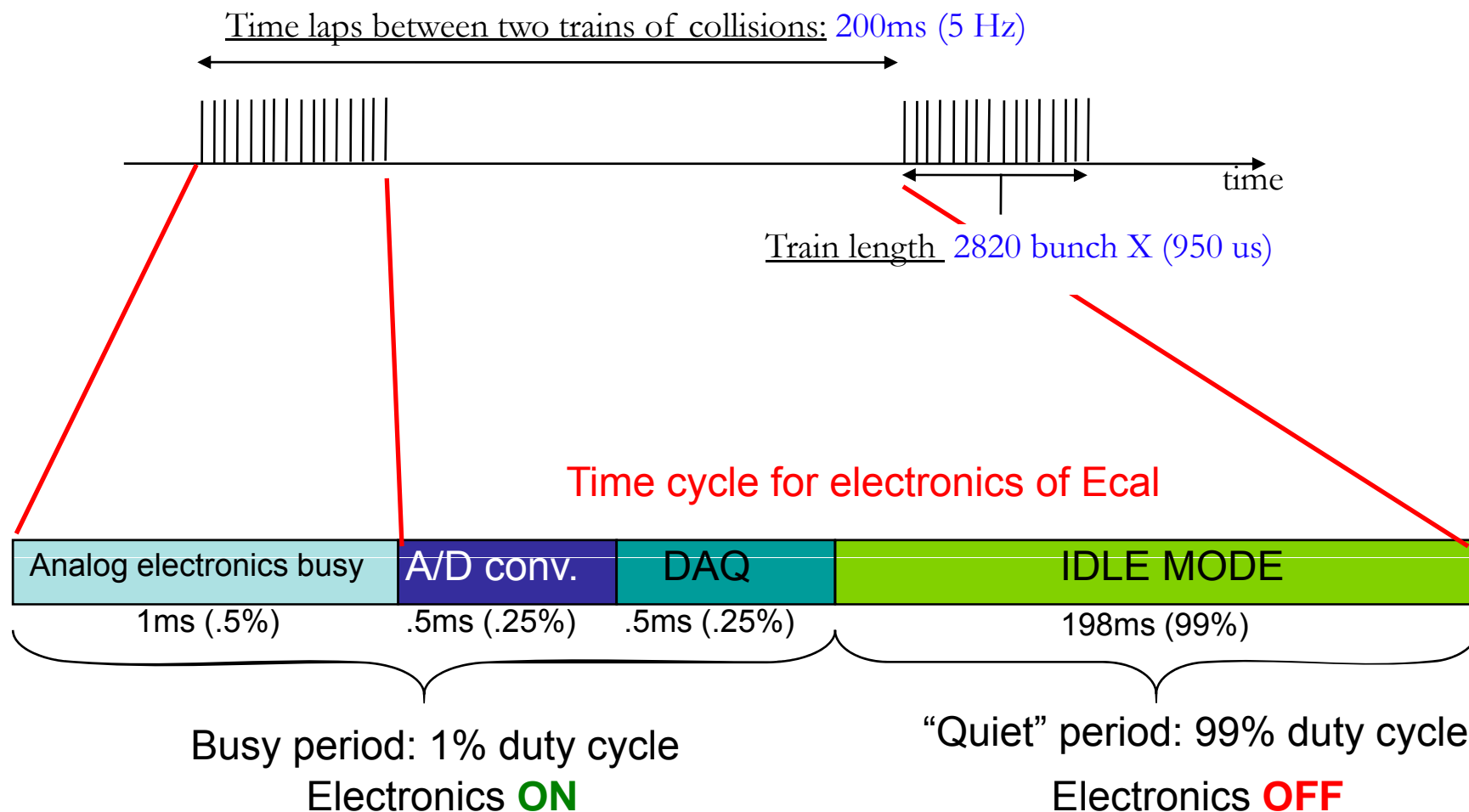
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The Silicon-Tungsten Ecal



- Sandwich structure of: thin wafers of silicon diodes ($\sim 200 \mu\text{m}$) & tungsten layers
- High granularity : diode pad size of $5 \times 5 \text{ mm}^2$
- High segmentation : ~ 30 layers
- Embedded VFE electronics
- Minimal cooling available

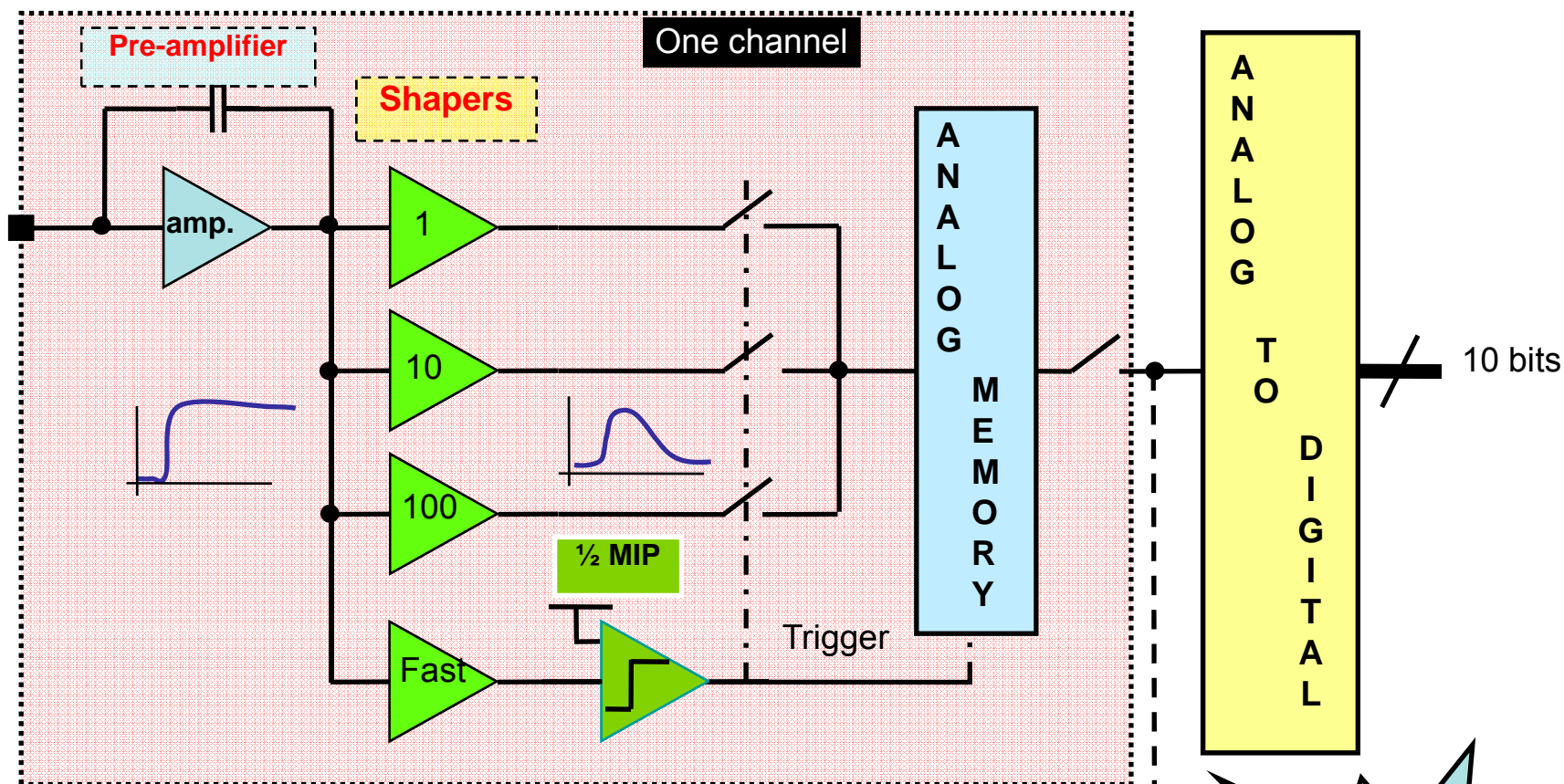




- Large dynamic range:
 - 0.1 MIP to 3000 MIP → 15 bits
- Precision of 8 bits
- Zero suppress on-chip
 - Auto-trigger on $\frac{1}{2}$ MIP
- Front-end embedded in detector
- $2 \cdot 10^8$ channels (5x5 mm² pads)
 - Compactness
- Ultra-low power : 25 μ W/ch max.
 - power pulsing: ON 2ms - OFF 198 ms



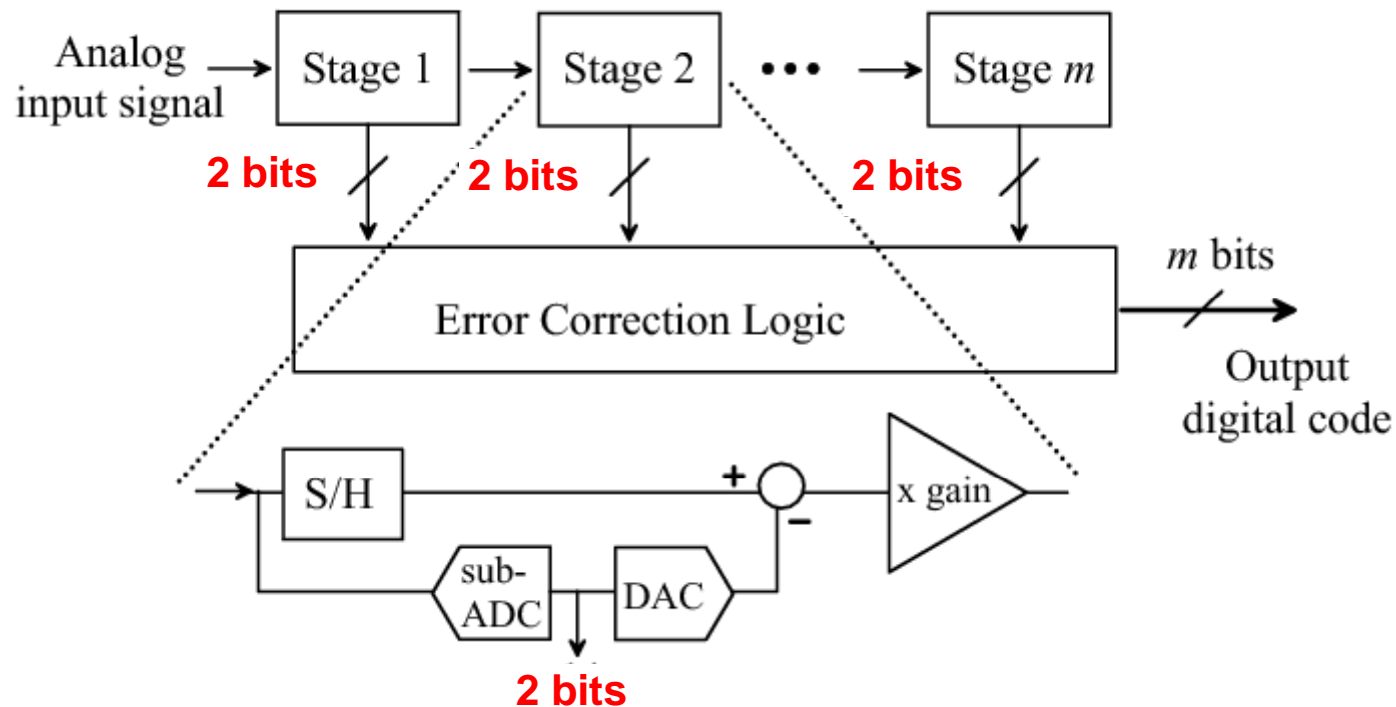
Ultra-low
POWER
is the
KEY issue
(C. de la Taille)



- LAL: Preamplifier, Shaper CRRC², Wilkinson ADC
- LPCC: Shaper gated integrator, pipeline ADC

- The **conversion operation is divided into m steps**, with m the number of bits of the output code. The most significant bits are resolved in the first step, and the least significant bits are resolved in the last step.
- **Each step is processed by a dedicated stage**; m -bits ADC $\rightarrow m$ stages
- Each stage converts the input signal into n bits (sub-ADC) and delivers an amplified residual voltage to the next stage.
- The Error Correction Logic Block processes the m n -bits to deliver the output digital code.

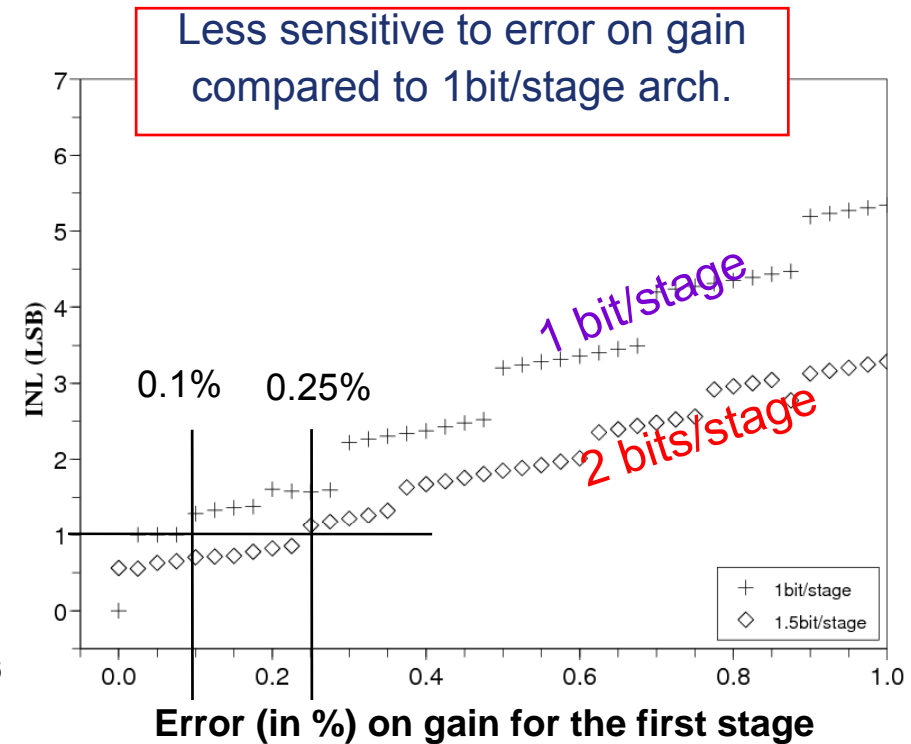
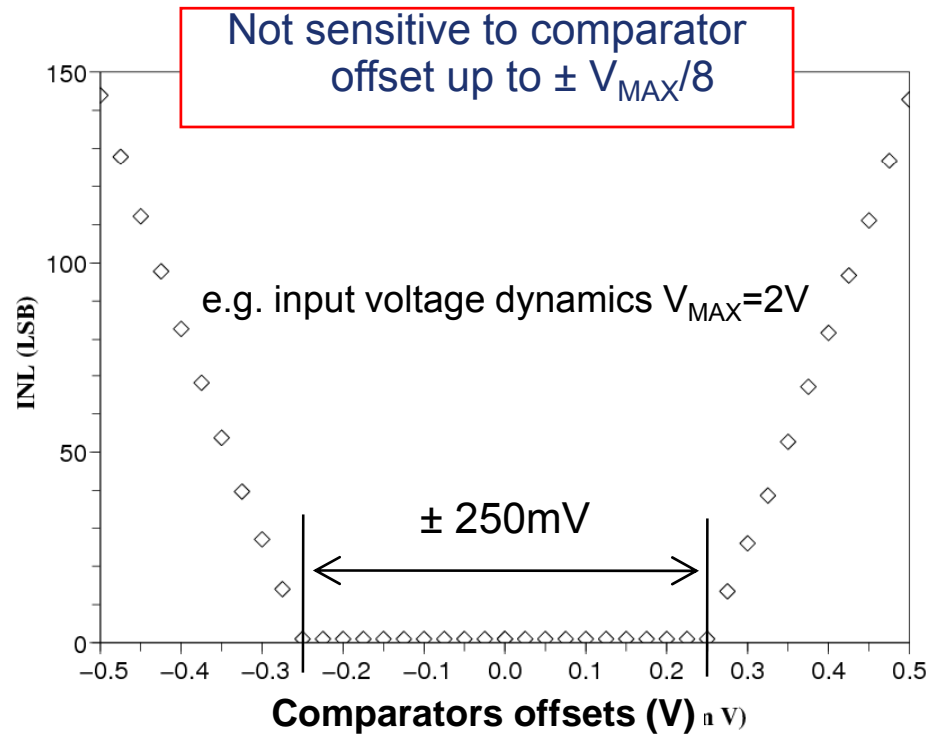
Linearity mainly affected by the comparator offset and the precision of the amplifier gain.



Why two bits per stage ?

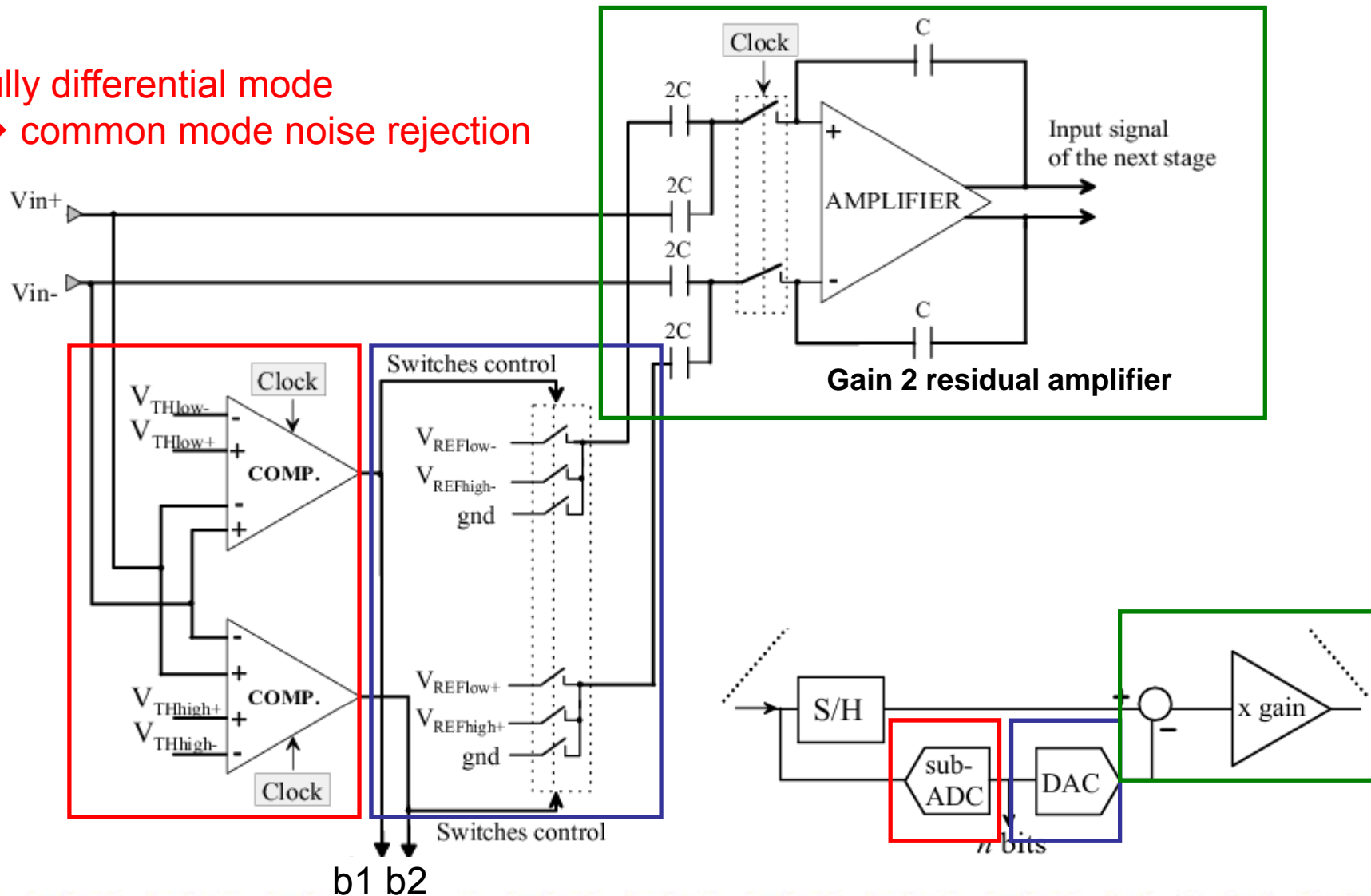


Algorithmic simulations
Integral NonLinearity (INL)

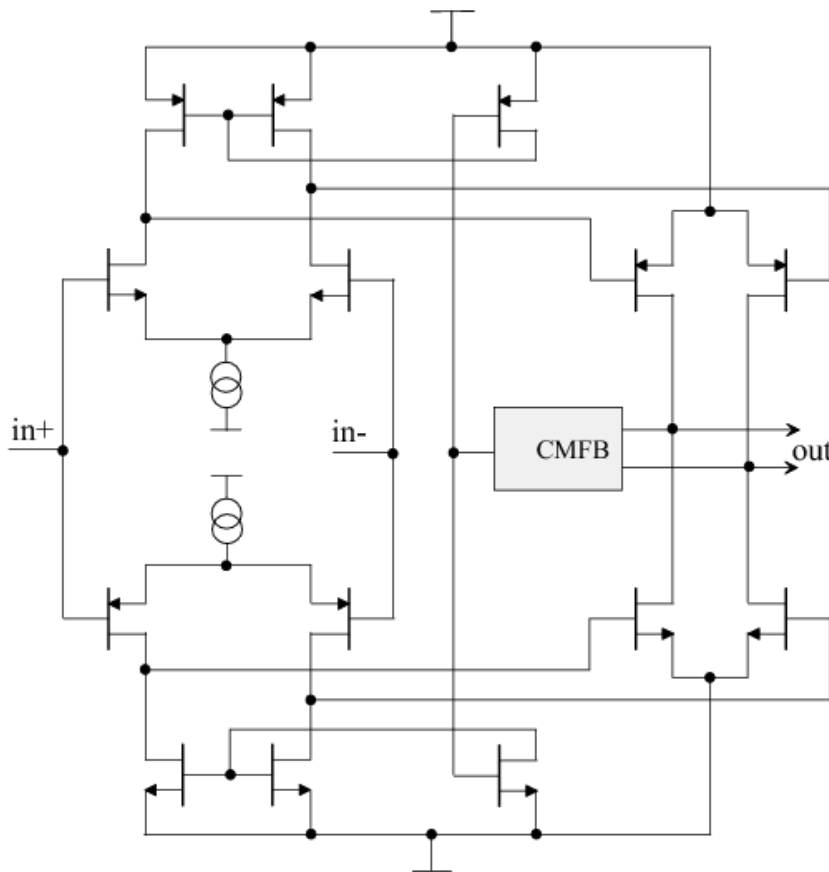


Arch. w/ a resolution of 2 bits per stage but the combination "11" avoided → 1.5 bit /stage

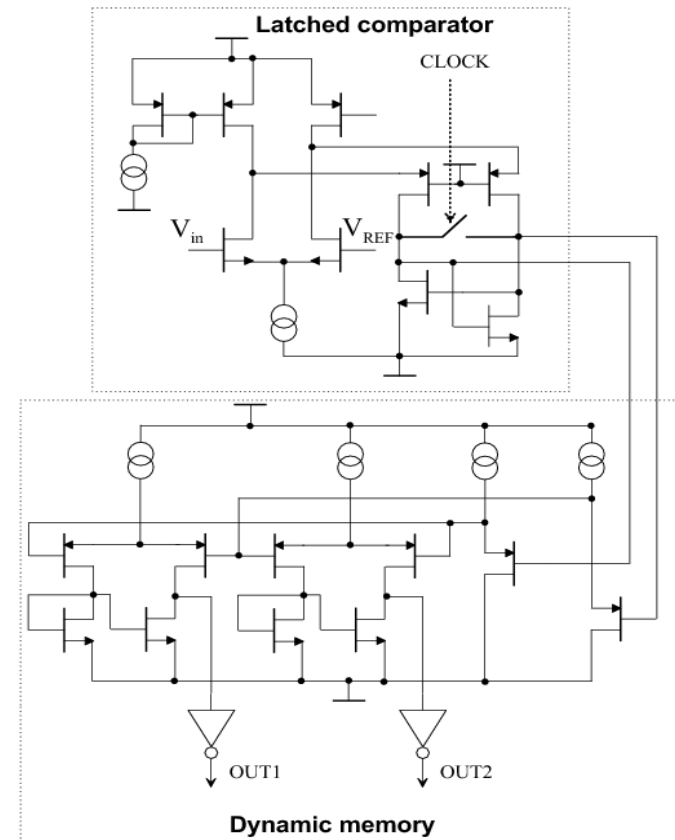
fully differential mode
→ common mode noise rejection



Amplifier and comparator



- **Amplifier**
- Fully differential and rail-to-rail
- **Gain-Bandwidth product: 50 MHz**
- Power consumption: 1.9 mW /5V

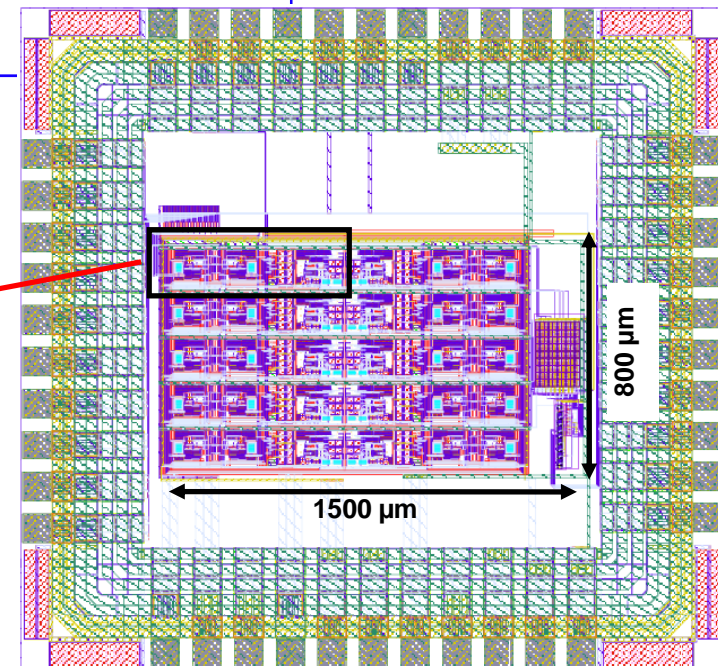
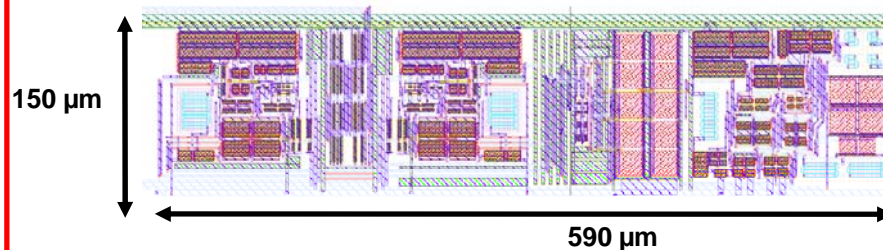


- **Comparator**
- Sensitivity = input noise : $< 280 \mu V$ (95% C.L.)
- **Offset: $(20 \pm 9) mV$ ($\pm 68\%$ C.L.)**
- Power consumption: $815 \mu W$ @ 4 MHz

Characteristics:

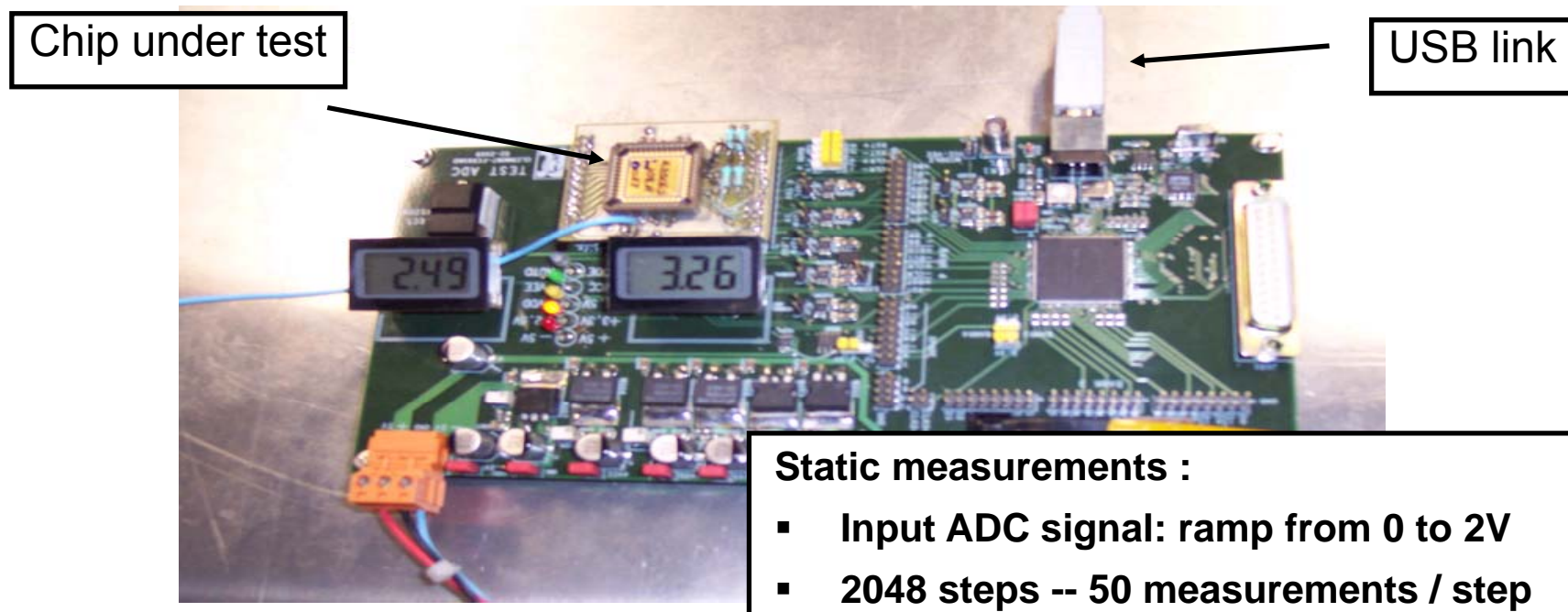
- 10 bits → 10 stages
- 1.5bit/stage and differential architecture
- Technology: Austriamicrosystems CMOS 0.35μm
- Power supply: 5V (digital: 2.5V)
- Clock (sampling) frequency: 4 MHz (MS/s)
- Die area: 1.2 mm²

Layout of 1 stage



Test Bench:

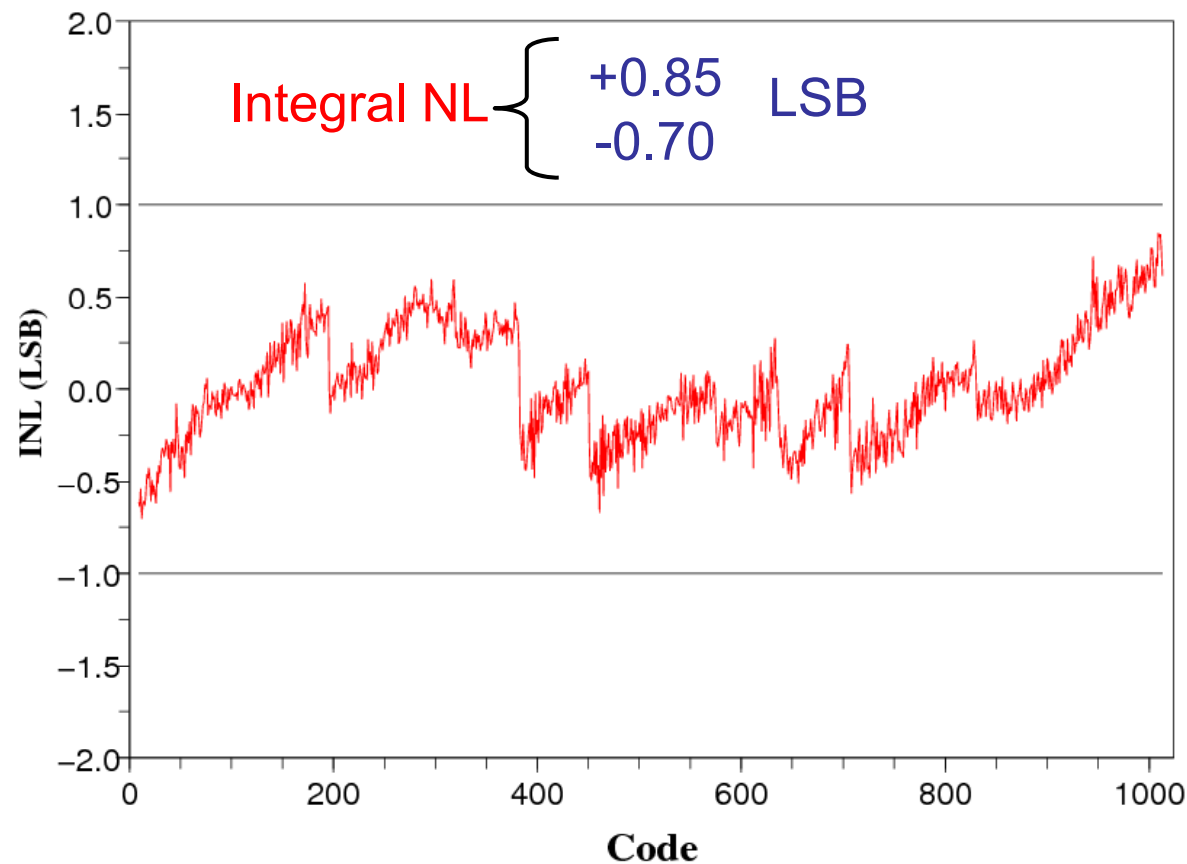
- Generic board for ADC tests
- Analogue signal generator: DAC 16 bits (DAC8830)
- PC/LabView Slow Control through USB interface
- Data processing with Scilab package



Linearity performance (1)



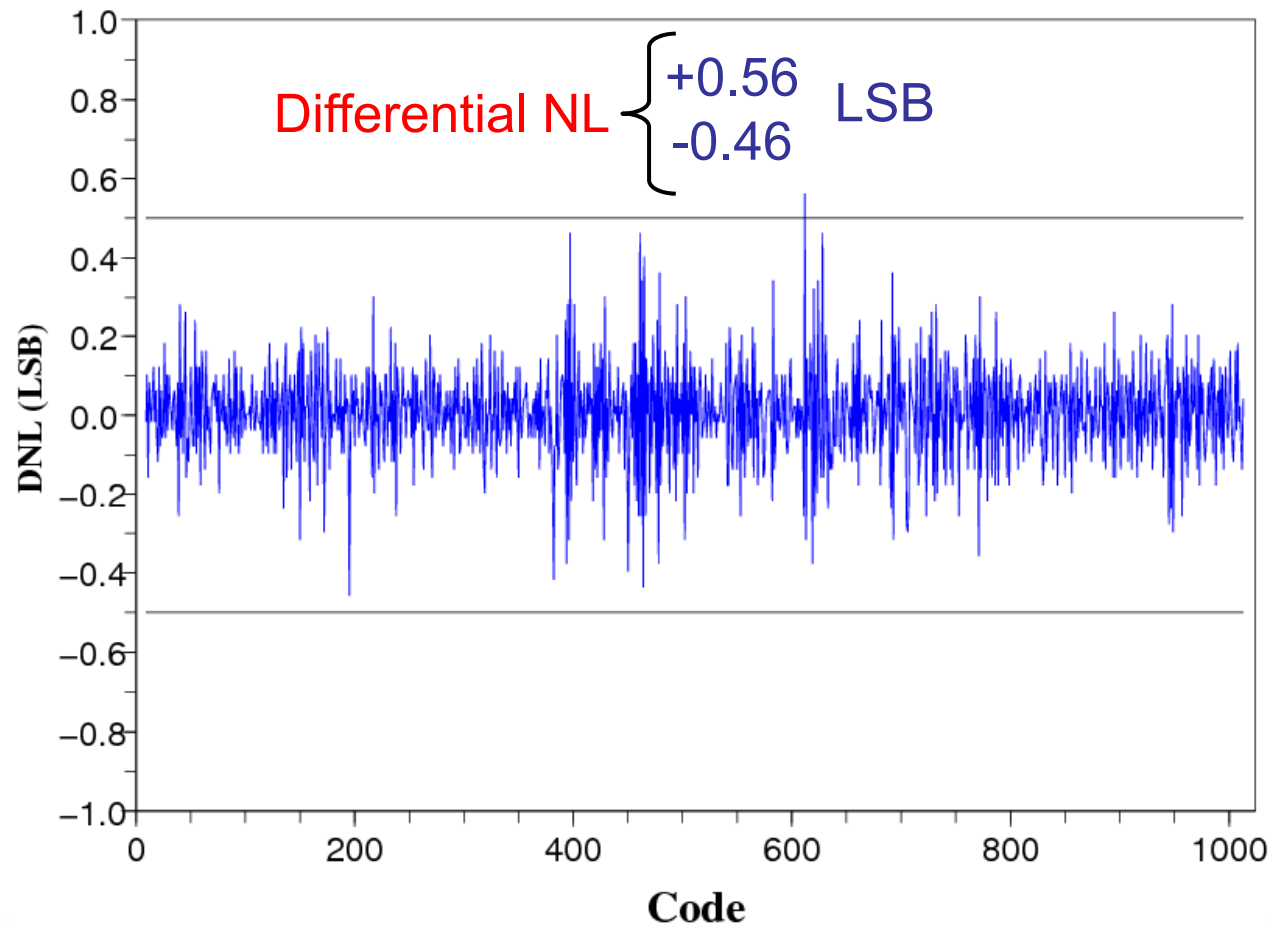
The Integral Non-Linearity (INL) refers to the deviation, in LSB, of each individual output code from the ideal transfer-function value.

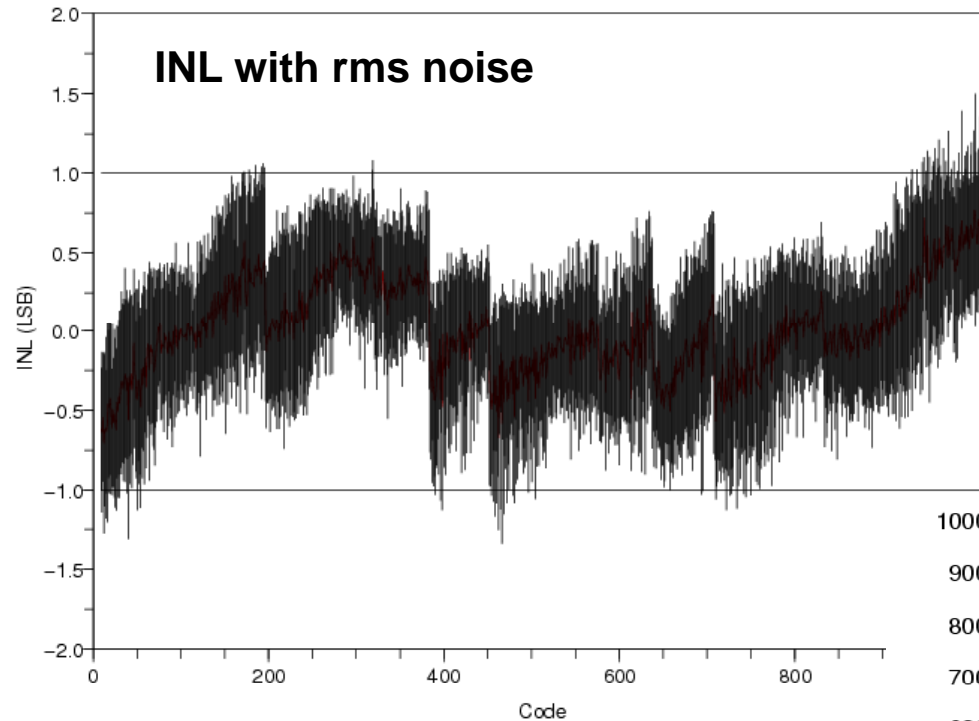


Linearity performance (2)

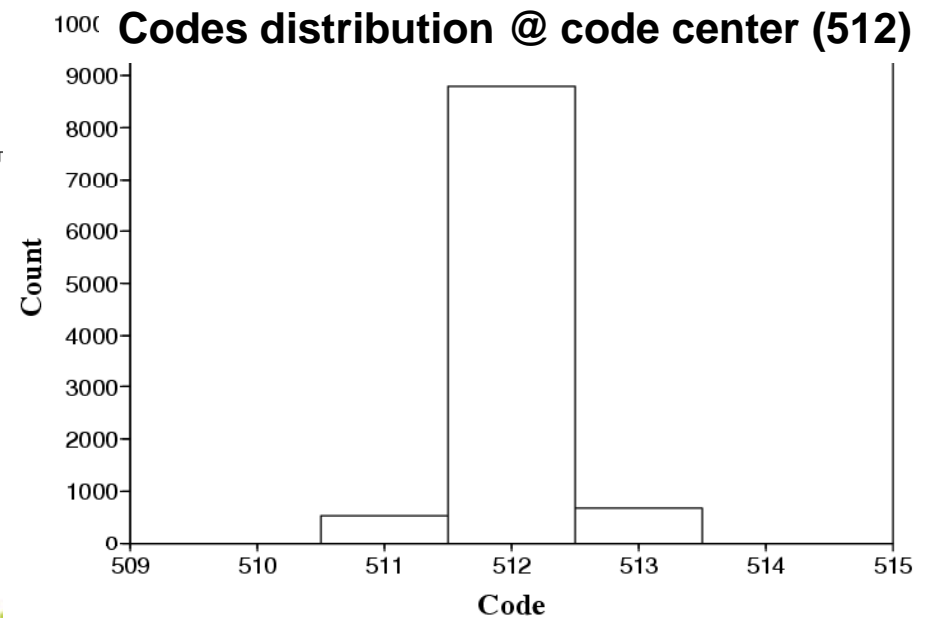


This Differential Non-Linearity (DNL) is defined as the difference between an actual step width and the ideal value of one LSB.





Measured noise
(including the setup noise):
< 0.5 LSB @ 68% C.L.



- Dynamic consumption : **35 mW** (clock @ 4MHz)
- Conversion time: 1 clock period = **250ns**
- Assuming:
 - 128 channels per VFE chip
 - 1 ADC per chip
 - 5 events max per channel (memory depth)
- ➡ With **power cycling**, the **integrated consumption** per channel of the A/D conversion can be estimated by:

$$\frac{P_w \times T_{conv} \times Mem.}{Time_cycle} = \frac{35mW \times 250ns \times 5}{200ms} = 0.22 \mu W/ch$$

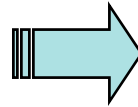
with

<i>P_w</i> :	power cons. of one channel
<i>T_{conv}</i> :	time for one conversion
<i>Mem</i> :	memory depth of one channel
<i>Time_{cycle}</i> :	time between two trains

The ON-setting time and pipeline latency effects can be neglected.

ADC requirements

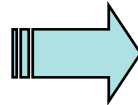
- 10 bits ADC precision



ADC measured performance

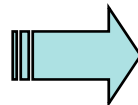
- ADC: precision of 10 bits
 - INL: -0.70/+0.85 LSB
 - DNL: -0.46/+0.56 LSB
 - Noise: <0.5 LSB

- Compactness



- One pipeline ADC per chip (128 ch)
- Die area of 1.2mm² for 128 ch.

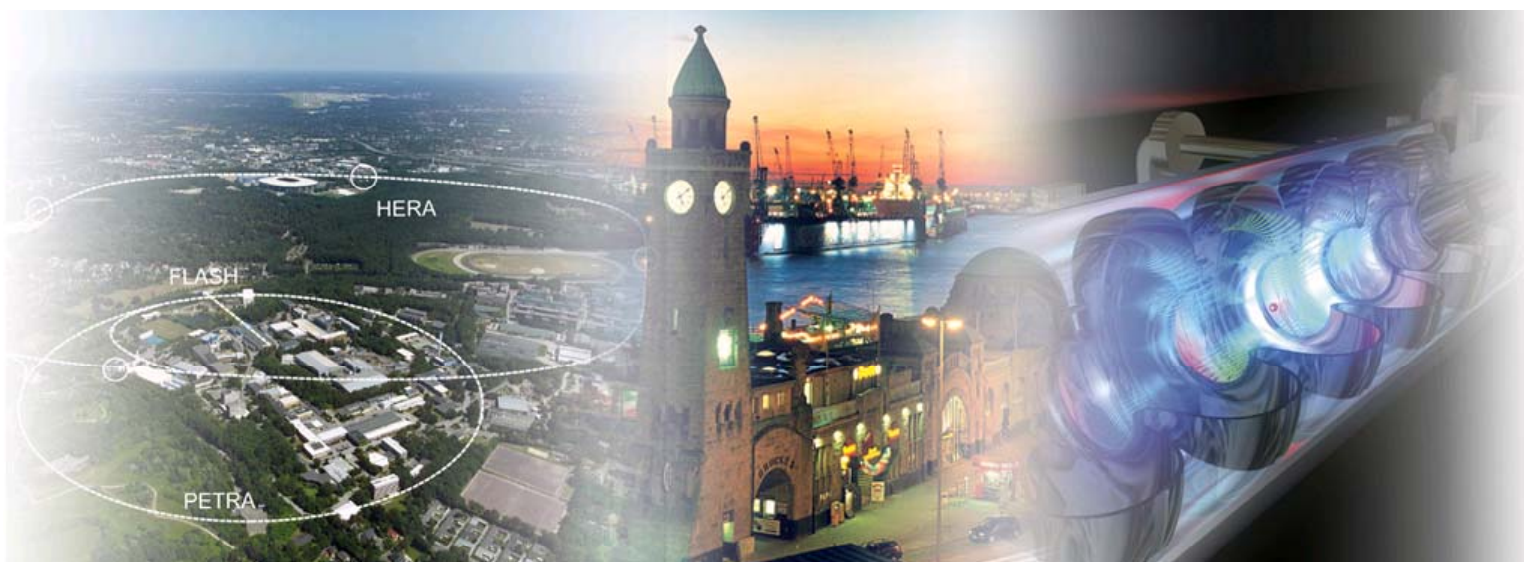
- Total cons. of VFE:
25 μ W/ch max



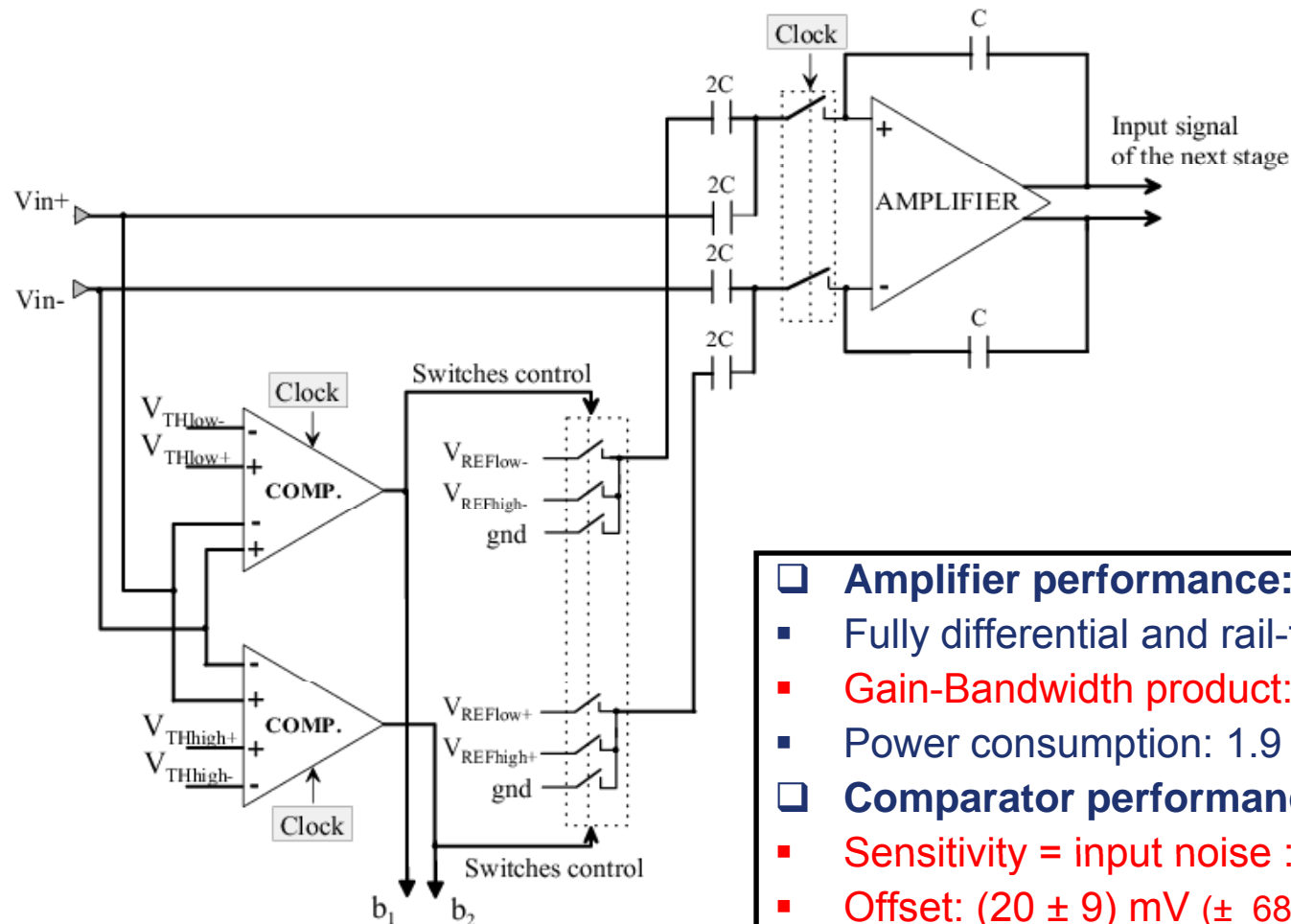
- Power cons.: 0.22 μ W/ch
 $\Rightarrow \approx 1\%$ total power of one channel

- Foreseen improvements:
 - Reduce power supply voltage (power cons.) from 5V to 3.5V (from 35mW to 25mW)**
 - Increase precision to 12 bits in order to have only a bi-gain shaping**
 - Implement and test the power pulsing**

A Pipeline **Analog-to-Digital Converter (ADC)** dedicated to the Ecal Very Front-End Electronics of ILC



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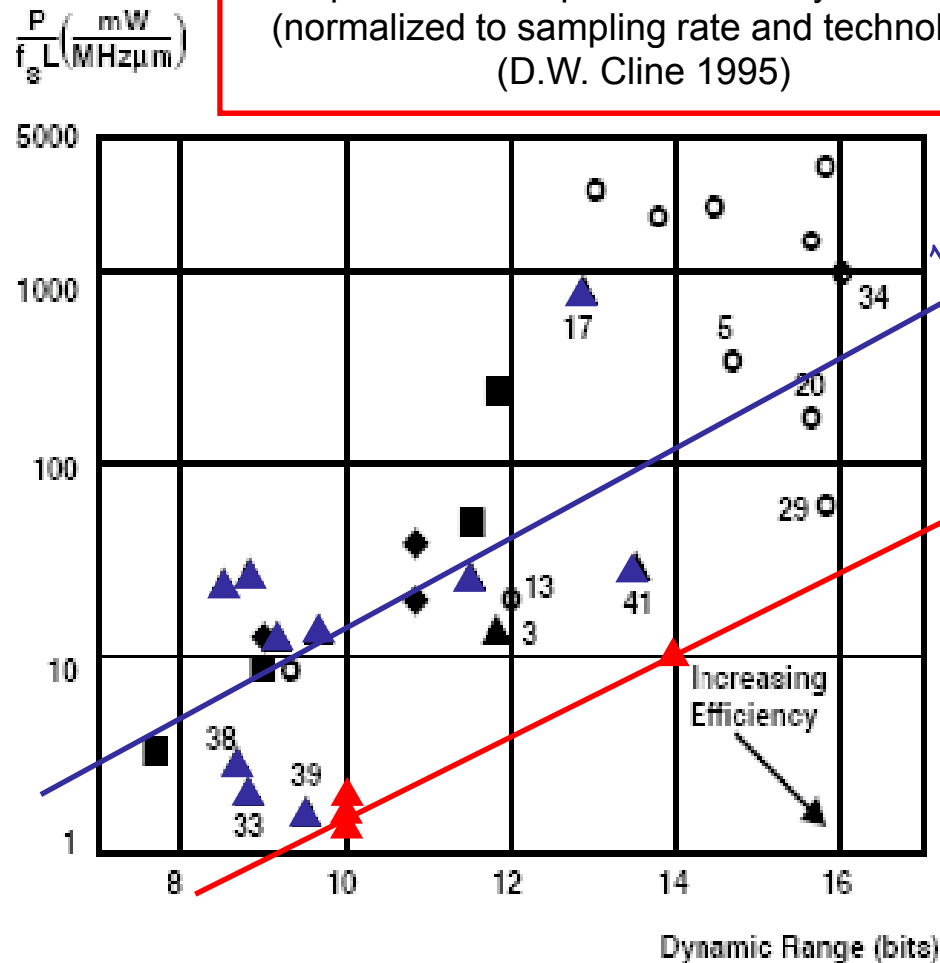
Amplifier performance:

- Fully differential and rail-to-rail
- **Gain-Bandwidth product: 50 MHz**
- Power consumption: 1.9 mW /5V

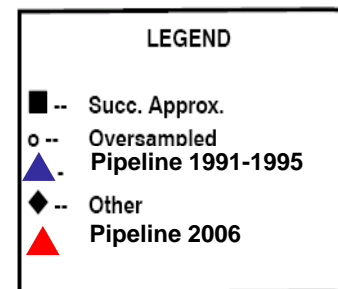
Comparator performance:

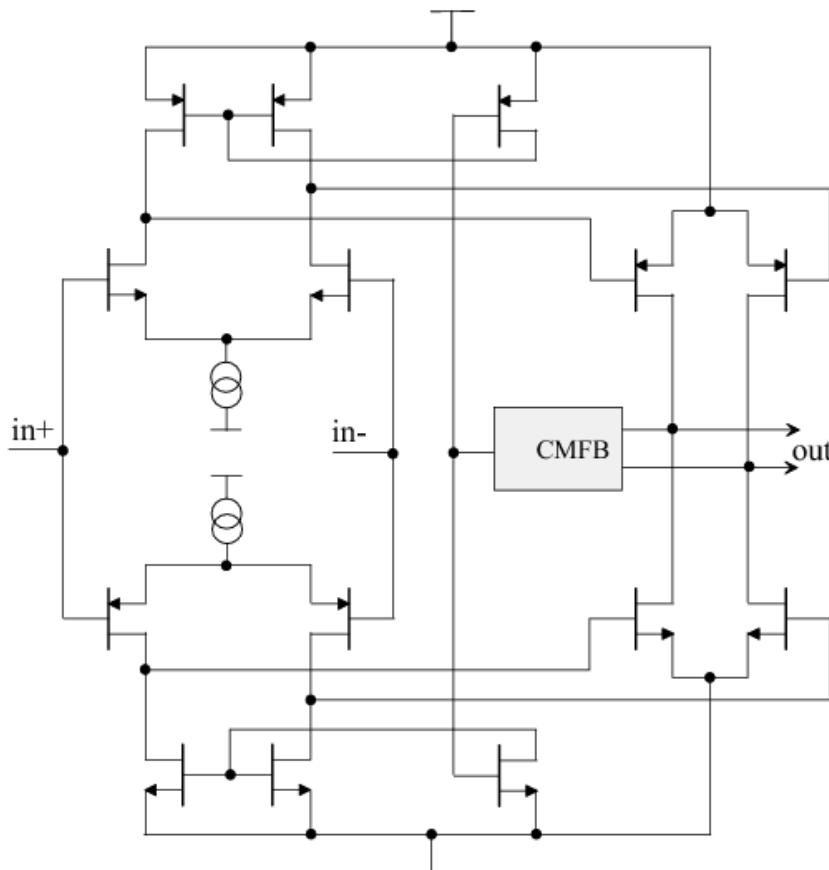
- **Sensitivity = input noise : < 280 μ V (95% C.L.)**
- **Offset: (20 \pm 9) mV (\pm 68% C.L.)**
- Power consumption: 815 μ W @ 4 MHz

Comparative ADC power versus dynamic range
(normalized to sampling rate and technology)
(D.W. Cline 1995)

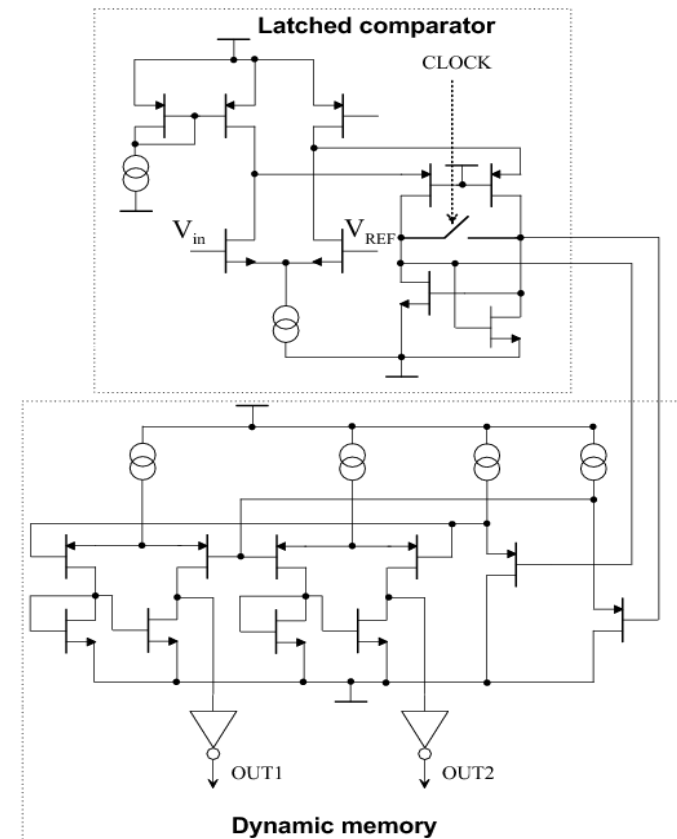


- Wide capabilities range for Pipeline ADCs (▲ ▲)
- Trade-off between:
- Resolution: 8 - 14 bits**
- Sampling rate: few MHz to hundreds of MHz**
- Consumption: few mW to tens of mW**
- Power divided by a factor 10 on ADC power in 10 years





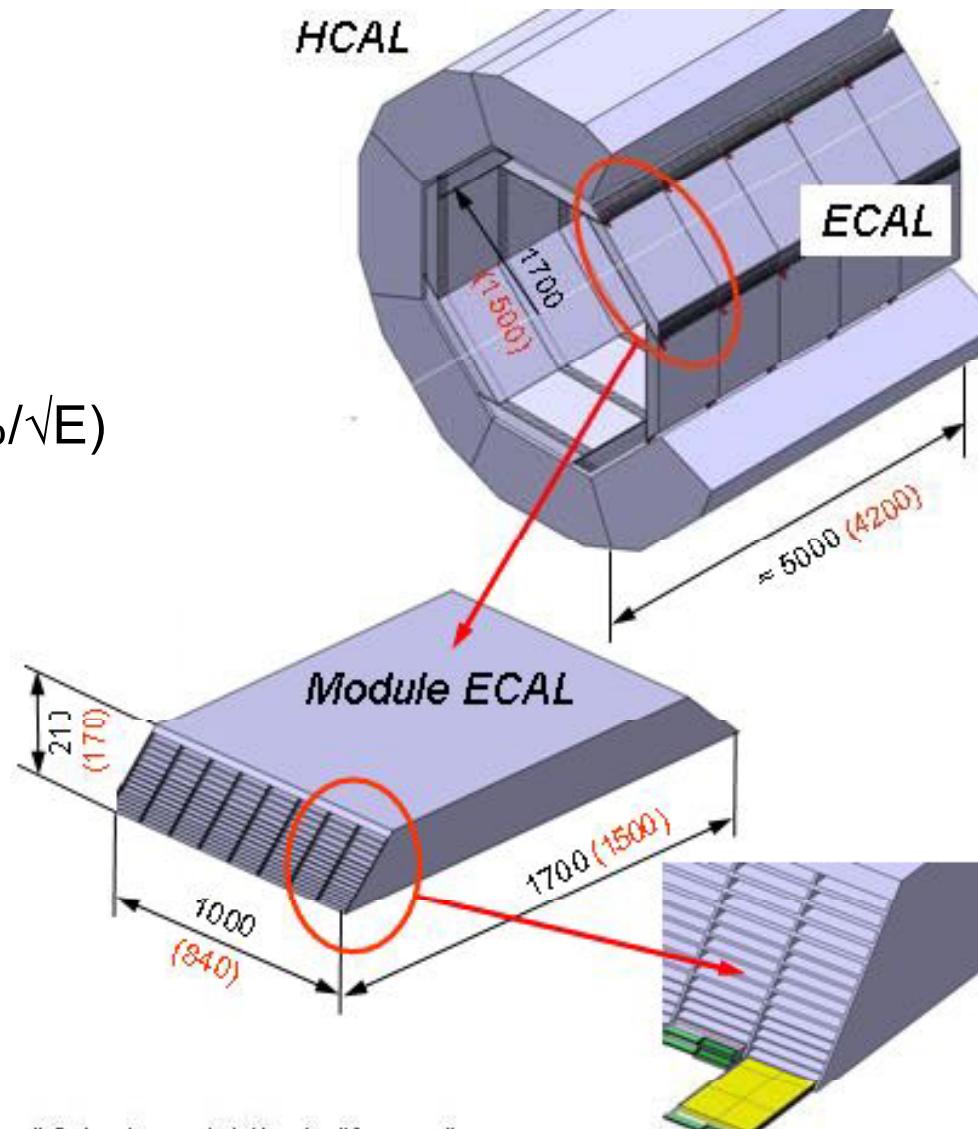
- **Amplifier**
 - Fully differential and rail-to-rail
 - Gain-Bandwidth product: 50 MHz
 - Power consumption: 1.9 mW /5V



Comparator

- Sensitivity = input noise : $< 280 \mu V$ (95% C.L.)
- Offset: $(20 \pm 9) mV$ ($\pm 68\%$ C.L.)
- Power consumption: $815 \mu W$ @ 4 MHz

- Measure photons and hadrons
- High granularity : typ $< 1 \text{ cm}^2$
- High segmentation : ~ 30 layers
- Moderate energy resolution ($10\%/\sqrt{E}$)



1.5 bit/stage pipeline architecture



- 2 comparators and one amplifier per stage required
- 2 threshold voltages and 3 reference voltages required

